Program of the IEE SAS Annual Seminar 2018

8:28 - 8:30	Opening remarks	Chair: V. Cambel
	Department of Superconductors	Chair: M. Grajcar
8:30 - 8:55	Presentation of research topics	
8:55 – 9:00	Discussion	
9:00 - 9:15	P. Kováč: Ultralight superconducting wire based on Mg, B, Ti and	Al
9:15 – 9:30	A. Rosová: Effects of high temperature HITEMAL annealing	
9:30 - 9:45	M. Kapolka: Demagnetization of Cubic Gd-Ba-Cu-O Bulk Supercon	ductor by Crossed-
	Fields	
9:45 – 10:00	E. Seiler: Critical current density of coated conductors determined	from rescaled
	magnetic moment at temperatures close to 77 K	
	Department of III-V Semiconductors	Chair: G. Vanko
10:10 - 10:35	Presentation of research topics	
10:35 – 10:40	Discussion	
10:40 - 10:55	S. Hasenöhrl: Generation of hole gas in non-inverted InAl(Ga)N/G	aN
	l	
	heterostructures (presented by J. Kuzmík)	
10:55 – 11:10	heterostructures (presented by J. Kuzmík) P. Chauhan: Effect of temperature and carrier gas on the properti	es of thick InAlN
10:55 – 11:10		es of thick InAIN
10:55 – 11:10 11:10 – 11:25	P. Chauhan: Effect of temperature and carrier gas on the properti	
	P. Chauhan: Effect of temperature and carrier gas on the propertilayer	

11:40 – 12:30 Lunch break

	Department of Physics and Technology at Nanoscale Chair: E. Pardo	
12:30 – 12:55	Presentation of research topics	
12:55 – 13:00	Discussion	
13:00 - 13:15	A. Mošková: States-conserving Altshuler-Aronov density of states	
13:15 – 13:30	M. Precner: Evolution of Metastable Defects and Its Effect on the Electronic	
	Properties of MoS₂ Films	
13:30 – 13:45	T. Ščepka: Ferromagnetic resonance study of sputtered Pt/Co/Pt multilayers	
13:45 – 14:00	K. Frohlich: <i>HfOx- and TaOx-based Resistive Switching Structures for Realization of</i>	
	Minimum and Maximum Functions	
	Department of Microelectronics and Sensors Chair: M. Ťapajna	
14:10 – 14:35	Presentation of research topics	
14:35 – 14:40	Discussion	
14:40 – 14:55	N. Gál: Simulation of Resistance Anomalies at Superconducting	
	Transition of N/S/F heterostructures	
14:55 – 15:10	M. Sojková:Horizontally and vertically aligned MoS₂ films grown on different	
	substrates	
15:10 – 15:25	Z. Zápražný:Nanomachining technology of active surfaces for new generation of X-	
	ray crystal optics	
15:30 – 16:00		